We claim:

1. A power semiconductor element, comprising:

an emitter region;

a stop zone in front of the emitter region;

said emitter region and said stop zone having mutually opposite conductivities;

said stop zone having foreign atoms with at least one energy level within the band gap of the semiconductor and at least 200 meV away from a conduction band and a valence band of the semiconductor.

2. The power semiconductor element according to claim 1, wherein said foreign atoms in said stop zone include sulfur atoms.

3. The power semiconductor element according to claim 1, wherein said foreign atoms in said stop zone include selenium atoms.